

## 512Kx8 PLASTIC SRAM

### PLASTIC PLUS® FEATURES

- Access Times of 15, 20, 25ns
- Standard Commercial Off-The-Shelf (COTS) Memory Devices for Extended Temperature Range
- JEDEC Standard 36 pin Plastic SOJ Package
- Electrical and Speed Characteristics for:
  - Military Temperature (-55°C to +125°C)
  - Industrial Temperature (-40°C to +85°C)
- Burn-in and Temperature Cycling Available
- Organized as 512K x 8
- Center Power/Ground Pins (Revolutionary)
- 5 Volt Power Supply
- Low Power ("L") Version Available
- Battery Back-Up Operation
- \* This product is subject to change without notice.

### **PIN CONFIGURATION FOR WPS512K8X-XRJX**

Top View		
<b>Top View</b> 1   2   3   4   5   6   7   8   9   10   11   12   13   14	36 35 34 33 32 31 30 29 28 27 26 25 24 23	
15 16 17 18	22 21 20 19	

### **PIN DESCRIPTION**

A0-18	Address Inputs			
I/0A0-19	Data Input/Output			
WE#	Chip Select			
CS#	Output Enable			
OE#	Write Enable			
Vcc	+5.0V Power			
Vss	Ground			
NC	Not Connected			

White Electronic Designs

### **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Min	Мах	Unit
Operating Temperature (Mil.)	TA	-55	+125	°C
Operating Temperature (Ind.)	TA	-40	+85	°C
Storage Temperature	Tstg	-65	+150	°C
Signal Voltage Relative to Vss	VG	-0.5	V <sub>CC</sub> + 0.5	V
Supply Voltage	Vcc	-0.5	7.0	V

#### NOTES:

- Minimum DC voltage is -0.5V on input/output pins. During transitions, this level may undershoot to -2.0V for periods <20ns. Maximum DC voltage on input/output pins is Vcc + 0.5V which, during transitions, may overshoot to Vcc + 2.0V for periods <20ns.</li>
- Minimum DC input voltage on pins A9, OE#, and RESET is -0.5V. During voltage transitions, A9, OE#, and RESET may undershoot Vss to -2.0V for periods of up to 20ns. See Figure 6. Maximum DC input voltage on pin A9 is +12.5V which may overshoot to +13.5V for periods up to 20ns.
- Output shorted for no more than one second. No more than one output shorted at a time.

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a Stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### **RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Min	Мах	Unit
Supply Voltage	Vcc	4.5	5.5	V
Input High Voltage	Vih	2.2	V <sub>CC</sub> + 0.5	V
Input Low Voltage	VIL	-0.3	+0.8	V
Operating Temp. (Mil.)	TA	-55	+125	°C
Operating Temp. (Ind.)	TA	-40	+85	°C

### CAPACITANCE

TA = +25°C

Parameter	Symbol	Conditions	Мах	Unit
Input capacitance	CIN	VIN = 0V, f = 1.0 MHz	6	рF
Output capacitance	Соит	V <sub>IN</sub> = 0V, f = 1.0 MHz	8	pF

This parameter is guaranteed by design but not tested.

#### **TRUTH TABLE**

CS	WE#	OE#	Mode	I/O Pin	VCC Current
Н	Х	Х	Power Down	High-Z	I <sub>SB</sub>
L	Н	Н	Out Disable	High-Z	lcc
L	Н	L	Read	Dout	lcc
L	L	Х	Write	DIN	lcc

### **DC CHARACTERISTICS**

Vcc = 5.0V, Vss = 0V, TA = -55 +125°C

Parameter	Symbol	Conditions	Min	Мах	Unit
Input Leakage Current	lu	Vcc = 5.5, VIN = Vss to Vcc		10	μA
Output Leakage Current	ILO	CS = VIH, OE = VIH, VOUT = VSS to VCC		10	μA
Vcc Read Current (1, 2)	lcc	CS = V <sub>IL</sub> , OE = V <sub>IH</sub> , f = 5MHz, Vcc = 5.5		180	mA
Vcc Standby Current (2, 5)	IBS	CS = V <sub>IH</sub> , OE = V <sub>IH</sub> , f = 5MHz, Vcc = 5.5		15	μA
Output Low Voltage	Vol	Iol = 8.0MA, Vcc = 4.5		0.4	V
Output High Voltage	Vон	Іон = -4.0мА, Vcc = 4.5	2.4		V

NOTES: DC test conditions: VIL = 0.3V, VIH = Vcc -0.3V

### Data Retention Characteristics (WPS512K8L-XRJX Only)

 $(TA = -55^{\circ}C TO + 125^{\circ}C)$ 

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Data Retention Supply Voltage	lu	Vcc = 5.5, VIN = Vss to Vcc	2.0		5.5	V
Low Power Data Retention	Ilo	CS = VIH, OE = VIH, VOUT = VSS to VCC		300	800	μA

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### **AC CHARACTERISTICS**

(V<sub>CC</sub> = 5.0V, V<sub>SS</sub> = 0V, TA = -55°C TO +125°C)

Parameter	Symbol	-1	5+	-:	20	-:	25	Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	trc	15		20		25		ns
Address Access Time	taa		15		20		25	ns
Output Hold from Address Change	toн	0		0		0		ns
Chip Select Access Time	tacs		15		20		25	ns
Output Enable to Output Valid	toe		8		10		12	ns
Chip Select to Output in Low Z	tcLZ <sup>1</sup>	3		3		3		ns
Output Enable to Output in Low Z	toLZ <sup>1</sup>	0		0		0		ns
Chip Disable to Output in High Z	tcHz <sup>1</sup>		7		8		10	ns
Output Disable to Output in High Z	tонz <sup>1</sup>		7		8		10	ns

\* 15ns bit available in the lower power option

NOTES:

1. This parameter is guaranteed by design but not tested

### **AC CHARACTERISTICS**

 $V_{CC} = 5.0V$ , GND = 0V, -55°C  $\leq T_A \leq +125$ °C

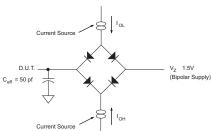
Parameter	Symbol	-1	5⁺	-2	20	-2	25	Unit
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	twc	15		20		25		ns
Chip Select to End of Write	tcw	12		12		15		ns
Address Valid to End of Write	taw	12		12		15		ns
Data Valid to End of Write	tow	8		9		10		ns
Write Pulse Width	twp	12		13		15		ns
Address Setup Time	tas	0		0		0		ns
Address Hold Time	tан	0		0		0		ns
Output Active from End of Write	tow <sup>1</sup>	0		0		0		ns
Write Enable to Output in High Z	twHz <sup>1</sup>		8		8		10	ns
Data Hold Time	tон	0		0		0		ns

\* 15ns bit available in the lower power option

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### AC TEST CONDITIONS

Parameter	Тур	Unit
Input Pulse Levels	VIL = 0, VIH = 3.0	V
Input Rise and Fall	5	ns
Input and Output Reference Level	1.5	V
Output Timing Reference Level	1.5	V

Notes:

VZ is programmable from -2V to +7V.

IOL & IOH programmable from 0 to 16mA.

Tester Impedance Z0 = 75  $\Omega$ .

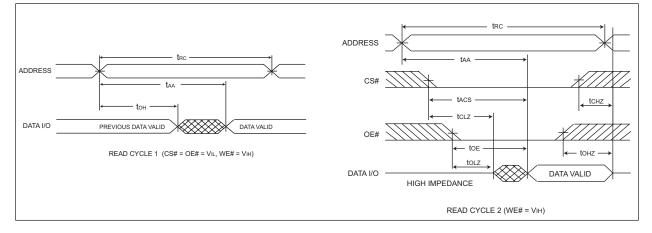
VZ is typically the midpoint of VOH and VOL.

IOL & IOH are adjusted to simulate a typical resistive load circuit.

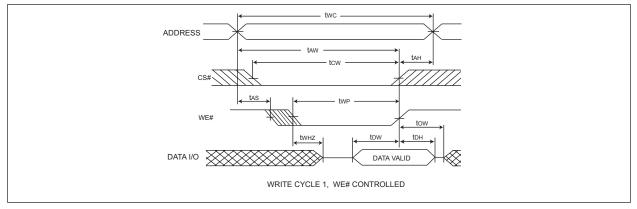
ATE tester includes jig capacitance.



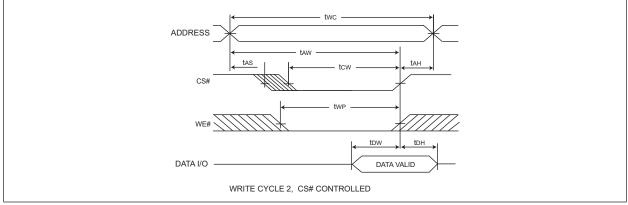
### **TIMING WAVEFORM - READ CYCLE**



### WRITE CYCLE - WE# CONTROLLED

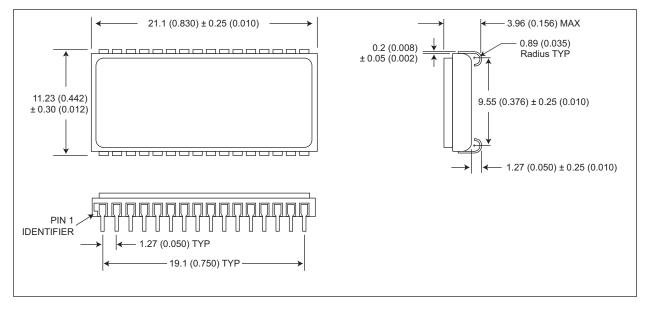


### WRITE CYCLE - CS# CONTROLLED



# WHITE ELECTRONIC DESIGNS

### PACKAGE 101: 32 LEAD, CERAMIC SOJ



### **ORDERING INFORMATION**

SRAM	
ORGANIZATION, 512K x 8	
Blank = Standard Power	
L = Low Power	
IMPROVEMENT MARK: B = Burn-in T = Temperature Cycling C = Burn-in and Temperature Cycle	
ACCESS TIME (ns):	
PACKAGE: RJ = Revolutionary	
DEVICE GRADE:M = Military Temperature-55°C to +125°CI = Industrial Temperature-40°C to +85°C	